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 Sheet 1 of 1

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126868		APPLICATION NO. New U.S. National Stage of PCT/JP2004/017562	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Masateru NAKAMURA			
				FILING DATE January 31, 2006			
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
	1.	US 4,349,407	9/14/1982	Lundberg			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	2.	JP A 2000-264790	9/26/2000	JAPAN	X	X	
	3.	JP A 2004-315281	11/11/2004	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	4.	Hoffman, D. H., et al. "Prospects of the use of liquid phase techniques for the growth of bulk silicon carbide crystals" MATERIALS SCIENCE AND ENGINEERING B, ELSEVIER SEQUOIA, LAUSANNE, CH, vol. 61-62, 30 July 1999 (1999-07-30), pages 29-39, XP004363298 ISSN: 0921-5107.					
EXAMINER				DATE CONSIDERED			
/Melissa Stalder/				11/04/2008			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: January 31, 2006

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /M.S./